FAIRCHILD

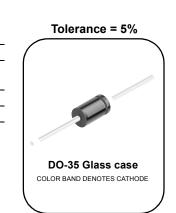
SEMICONDUCTOR®

Zeners 1N5985B - 1N6025B

Absolute Maximum Ratings * T_A = 25°C unless otherwise noted

	C			
Symbol	Parameter	Value	Units	
PD	Power Dissipation @ TL \leq 75°C, Lead Length = 3/8"	500	mW	
	Derate above 75°C	4.0	mW/°C	
T _J , T _{STG}	Operating and Storage Temperature Range	-65 to +200	°C	

* These ratings are limiting values above which the serviceability of the diode may be impaired.



Zeners 1N5985B - 1N6025B

Electrical Characteristics T_A=25°C unless otherwise noted

V _Z (V) @ I _Z (N		te 1) Test Current		Zener Impedance		leakage Current			
Device	Min.	Тур.	Max.	I _Z (mA)	Z _Z @ I _Z (Ω)	Z _{ZK} @ I _{ZK} = 250μA (Ω)	l _R (mA)	V _R (V)	IZM (MA (Note 2)
1N5985B	2.58	2.4	2.52	5	100	1800	100	1	208
1N5986B	2.565	2.7	2.835	5	100	1900	75	1	185
1N5987B	2.85	3	3.15	5	95	2000	50	1	167
1N5988B	3.135	3.3	3.465	5	95	2200	25	1	152
1N5989B	3.42	3.6	3.78	5	90	2300	15	1	139
1N5990B	3.705	3.9	4.095	5	90	2400	10	1	128
1N5991B	4.085	4.3	4.515	5	88	2500	5	1	116
1N5992B	4.465	4.7	4.935	5	70	2200	3	1.5	106
1N5993B	4.845	5.1	5.355	5	50	2050	2	2	98
1N5994B	5.32	5.6	5.88	5	25	1800	2	3	89
1N5995B	5.89	6.2	6.51	5	10	1300	1	4	81
1N5996B	6.46	6.8	7.14	5	8	750	1	5.2	74
1N5997B	7.125	7.5	7.875	5	7	600	0.5	6	67
1N5998B	7.79	8.2	8.61	5	7	600	0.5	6.5	61
1N5999B	8.645	9.1	9.555	5	10	600	0.1	7	55
1N6000B	9.5	10	10.5	5	15	600	0.1	8	50
1N6001B	10.45	11	11.55	5	18	600	0.1	8.4	45
1N6002B	11.4	12	12.6	5	22	600	0.1	9.1	42
1N6003B	12.35	13	13.65	5	25	600	0.1	9.9	38
1N6004B	14.25	15	15.75	5	32	600	0.1	11	33
1N6005B	15.2	16	16.8	5	36	600	0.1	12	31
1N6006B	17.1	18	18.9	5	42	600	0.1	14	28
1N6007B	19	20	21	5	48	600	0.1	15	25
1N6008B	20.9	22	23.1	5	55	600	0.1	17	23
1N6009B	22.8	24	25.2	5	62	600	0.1	18	21
1N6010B	25.65	27	28.35	5	70	600	0.1	21	19
1N6011B	28.5	30	31.5	5	78	600	0.1	23	17
1N6012B	31.35	33	34.65	5	88	700	0.1	25	15
1N6013B	34.2	36	37.8	5	95	700	0.1	27	14
1N6014B	37.05	39	40.95	2	130	800	0.1	30	13

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V _z ((V) @ I _Z (Note 1)		Test	Zener Impedance		leakage Current		
Device	Min.	Тур.	Max.	Test Current I _Z (mA)	Z _Z @ I _Z (Ω)	Z _{ZK} @ I _{ZK} = 250μA (Ω)	l _R (mA)	V _R (V)	I _{ZM} (mA) (Note 2)
1N6015B	40.85	43	45.15	2	150	900	0.1	33	12
1N6016B	44.65	47	49.35	2	170	1000	0.1	36	11
1N6017B	48.45	51	53.55	2	180	1300	0.1	39	9.8
1N6018B	53.2	56	58.8	2	200	1400	0.1	43	8.9
1N6019B	58.9	62	65.1	2	225	1400	0.1	47	8
1N6020B	64.6	68	71.4	2	240	1600	0.1	52	7.4
1N6021B	71.25	75	78.75	2	265	1700	0.1	56	6.7
1N6022B	77.9	82	86.1	2	280	2000	0.1	62	6.1
1N6023B	86.45	91	95.55	2	300	2300	0.1	69	5.5
1N6024B	95	100	105	1	500	2600	0.1	76	5
1N6025B	104.5	110	115.5	1	650	3000	0.1	84	4.5

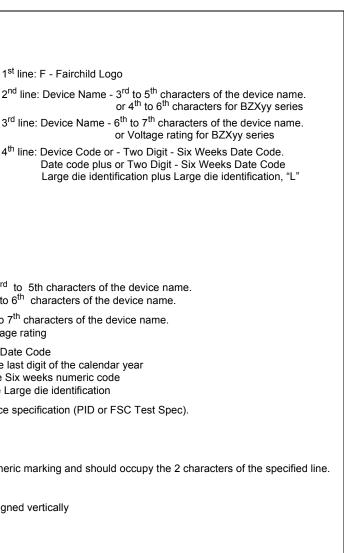
1 Zeners 1N5985B - 1N6025B

Notes:
1. Zener Voltage (V_Z)
The zener voltage is measured with the device junction in the themal equilibrium at the lead temperature (T_L) at 30°C ± 1°C and 3/8" lead length.

2. Maximum Zener Current Ratings (I_{ZM})
The maximum current handling capability on a worst case basis is limited by the actual zener voltage at the operation point and the power derating curve.

Device	Line 1	Line 2	Line 3	Line 4
5985B	LOGO	598	5B	XY
5986B	LOGO	598	6B	XY
5987B	LOGO	598	7B	XY
5988B	LOGO	598	8B	XY
5989B	LOGO	598	9B	XY
5990B	LOGO	599	0B	XY
5991B	LOGO	599	1B	XY
5992B	LOGO	599	2B	XY
5993B	LOGO	599	3B	XY
5994B	LOGO	599	4B	XY
5995B	LOGO	599	5B	XY
5996B	LOGO	599	6B	XY
5997B	LOGO	599	7B	XY
5998B	LOGO	599	8B	XY
5999B	LOGO	599	9B	XY
6000B	LOGO	600	0B	XY
6001B	LOGO	600	1B	XY
6002B	LOGO	600	2B	XY
6003B	LOGO	600	3B	XY
6004B	LOGO	600	4B	XY
005B	LOGO	600	5B	XY
6006B	LOGO	600	6B	XY
007B	LOGO	600	7B	XY
6008B	LOGO	600	8B	XY
3009B	LOGO	600	9B	XY
010B	LOGO	601	0B	XY
6011B	LOGO	601	1B	XY
6012B	LOGO	601	2B	XY
6013B	LOGO	601	3B	XY
6014B	LOGO	601	4B	XY
6015B	LOGO	601	5B	XY
6016B	LOGO	601	6B	XY
6017B	LOGO	601	7B	XY
6018B	LOGO	601	8B	XY
6019B	LOGO	601	9B	XY
020B	LOGO	602	0B	XY
6021B	LOGO	602	1B	XY
6022B	LOGO	602	2B	XY
6023B	LOGO	602	3B	XY
6024B	LOGO	602	4B	XY
6025B	LOGO	602	5B	XY

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General Requirements:

Top Mark Information (Continued)

9B

1.0 Cathod Band

2.0 First Line: F - Fairchild Logo

3.0 Second Line: Device name - For 1Nxx series: 3rd to 5th characters of the device name. For BZxx series: 4th to 6th characters of the device name.

4.0 Third Line: Device name - For 1Nxx series: 6th to 7th characters of the device name. For BZXyy series: Voltage rating

5.0 Fourth Line: XY or XYL - Two Digit - Six Weeks Date Code Where: X represents the last digit of the calendar year Y represents the Six weeks numeric code L represents the Large die identification

6.0 Devices shall be marked as required in the device specification (PID or FSC Test Spec).

7.0 Maximum no. of marking lines: 4

8.0 Maximum no. of digits per line: 3

9.0 FSC logo must be 20 % taller than the alphanumeric marking and should occupy the 2 characters of the specified line.

10.0 Marking Font: Arial (Except FSC Logo)

11.0 First character of each marking line must be aligned vertically

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Bottomless™	FASTr™	MICROCOUPLER™	PowerSaver™	SuperSOT™-3
CoolFET™	FPS™	MicroFET™	PowerTrench [®]	SuperSOT [™] -6
CROSSVOLT™	FRFET™	MicroPak™	QFET [®]	SuperSOT [™] -8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™່	MSX™	QT Optoelectronics [™]	TinyLogic [®]
E ² CMOS [™]	HiSeC™	MSXPro™	Quiet Series [™]	TINYOPTO™
EnSigna™	I ² C [™]	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect™	OCXPro™	RapidConnect™	UHC™
Across the boar	d. Around the world.™	OPTOLOGIC [®]	SILENT SWITCHER®	UltraFET [®]
The Power Fran		OPTOPLANAR™	SMART START™	VCX™
Programmable A		PACMAN™	SPM™	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

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First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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